

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	233	(semiconductor or wafer or substrate) and source and drain and p-type and n-type and (drain near4 drift) and (drain near4 contact) and dop\$4 and ((insulat\$4 or oxide or dielectric) near4 gate) and channel and strip\$4 and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 14:16
S2	8	(semiconductor or wafer or substrate) and source and drain and p-type and n-type and (drain near4 drift) and (drain near4 contact) and dop\$4 and ((insulat\$4 or oxide or dielectric) near4 gate) and channel and strip\$4 and voltage and localis\$4 and (trench or via of hole) and deplet\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 14:17